

PRODUCT DISCONTINUATION NOTICE - LAST TIME BUY EXPIRES MAY 6, 2017

GENERAL DESCRIPTION

The 844001 is a Fibre Channel Clock Generator. The 844001 uses an 18pF parallel resonant crystal over the range of 20.4MHz - 28.3MHz. For Fibre Channel applications, a 26.5625MHz crystal is used. The frequency select pin allows the device to generate either 106.25MHz or 212.5MHz from a 26.5625MHz crystal. To generate 187.5MHz for 12Gb Ethernet, a 23.4375MHz crystal is used. The 844001 uses IDT's 3rd generation low phase noise VCO technology and can achieve <1ps typical rms phase jitter, easily meeting Fibre Channel and Ethernet jitter requirements. The 844001 is packaged in a small 8-pin TSSOP, making it ideal for use in systems with limited board space.

NOTE: It is not recommended to overdrive the crystal input with an external clock.

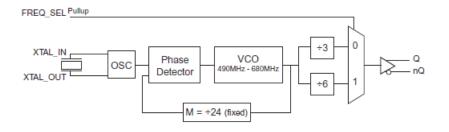
FEATURES

- · One Differential LVDS output
- Crystal oscillator interface, 18pF parallel resonant crystal (20.4MHz - 28.3MHz)
- Output frequency range: 81.66MHz 226.66MHz
- VCO range: 490MHz 680MHz
- RMS phase jitter @ 106.25MHz, using a 26.5625MHz crystal (637kHz - 10MHz): 0.74ps (typical)
- 3.3V or 2.5V operating supply
- 0°C to 70°C ambient operating temperature
- Available in lead-free (RoHS 6) package
- For functional replacement part use 8T49N242

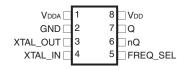
COMMON CONFIGURATION TABLE - FIBRE CHANNEL, 12Gb ETHERNET

	Inputs						
Crystal Frequency (MHz)	FREQ_SEL	М	N	Multiplication Value M/N	Output Frequency (MHz)		
26.5625	1	24	6	4	106.25		
26.5625	0	24	3	8	212.5		
23.4375	0	24	3	8	187.5		

BLOCK DIAGRAM



PIN ASSIGNMENT



844001

8-Lead TSSOP 4.40mm x 3.0mm x 0.925mm package body G Package Top View



TABLE 1. PIN DESCRIPTIONS

Number	Name	Ту	ре	Description
1	V _{DDA}	Power		Analog supply pin.
2	GND	Power		Power supply ground.
3, 4	XTAL_OUT, XTAL_IN	Input		Crystal oscillator interface. XTAL_IN is the input, XTAL_OUT is the output.
5	FREQ_SEL	Input	Pullup	Frequency select pin.
6, 7	nQ, Q	Output		Differential clock outputs. LVDS interface levels.
8	V _{DD}	Power		Core supply pin.

NOTE: Pullup refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C	Input Capacitance			4		pF
R	Input Pullup Resistor			51		kΩ



ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V 4.6V

Inputs, V -0.5V to $V_{DD} + 0.5 V$

Outputs, I_o (LVDS) Continuous Current 10mA 15mA Surge Current

Package Thermal Impedance, θ_{la} 101.7°C/W (0 mps)

Storage Temperature, T_{sta} -65°C to 150°C NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the DC Characteristics or AC Characteristics is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Table 3A. Power Supply DC Characteristics, $V_{DD} = V_{DDA} = 3.3V \pm 5\%$, $TA = 0^{\circ}C$ to $70^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Core Supply Voltage		3.135	3.3	3.465	V
V _{DDA}	Analog Supply Voltage		V _{DD} - 0.12	3.3	V _{DD}	V
I _{DD}	Power Supply Current				115	mA
DDA	Analog Supply Current				12	mA

Table 3B. Power Supply DC Characteristics, $V_{_{DD}} = V_{_{DDA}} = 2.5V \pm 5\%$, Ta = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Core Supply Voltage		2.375	2.5	2.625	V
V _{DDA}	Analog Supply Voltage		V _{DD} - 0.12	2.5	V	V
I _{DD}	Power Supply Current				110	mA
I _{DDA}	Analog Supply Current				12	mA

Table 3C. LVCMOS/LVTTL DC Characteristics, $V_{\tiny DD} = V_{\tiny DDA} = 3.3 V \pm 5\%$ or $2.5 V \pm 5\%$, Ta = 0° C to 70° C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V	Input High Voltage		$V_{_{DD}} = 3.3V$	2		V _{DD} + 0.3	V
V _{IH}	Imput riigir voitage		V _{DD} = 2.5V	1.7		V _{DD} + 0.3	V
v	Input Low Voltage		$V_{_{DD}} = 3.3V$	-0.3		0.8	V
l v _⊩	Imput Low voltage		$V_{_{DD}} = 2.5V$	-0.3		0.7	V
I _{IH}	Input High Current	FREQ_SEL	$V_{DD} = V_{IN} = 3.465 \text{V or } 2.625 \text{V}$			5	μA
I	Input Low Current	FREQ_SEL	$V_{_{DD}} = 3.465 \text{V or } 2.625 \text{V}, V_{_{IN}} = 0 \text{V}$	-150			μΑ

Table 3D. LVDS DC Characteristics, $V_{_{DD}} = V_{_{DDA}} = 3.3V \pm 5\%$, Ta = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{od}	Differential Output Voltage		350	415	480	mV
$\Delta V_{_{ m OD}}$	V _{op} Magnitude Change				50	mV
Vos	Offset Voltage		1.225	1.325	1.425	V
ΔV_{os}	V _{os} Magnitude Change				50	mV

NOTE: Please refer to Parameter Measurement Information for output information.



Table 3E. LVDS DC Characteristics, $V_{\text{dd}} = V_{\text{dda}} = 2.5V \pm 5\%$, Ta = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{od}	Differential Output Voltage		300	390	480	mV
Δ V $_{\scriptscriptstyle{OD}}$	V _{op} Magnitude Change				50	mV
Vos	Offset Voltage		1.0	1.2	1.325	V
ΔV_{os}	V _{os} Magnitude Change				50	mV

NOTE: Please refer to Parameter Measurement Information for output information.

TABLE 4. CRYSTAL CHARACTERISTICS

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		F	undamental		
Frequency		20.4		28.3	MHz
Equivalent Series Resistance (ESR)				50	Ω
Shunt Capacitance				7	pF
Drive Level				1	mW

NOTE: It is not recommended to overdrive the crystal input with an external clock.

Table 5A. AC Characteristics, $V_{_{DD}} = V_{_{DDA}} = 3.3V \pm 5\%, T_{A} = 0^{\circ}C$ to $70^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{out}	Output Frequency		81.66		226.66	MHz
		106.25MHz @ Integration Range: 637kHz - 10MHz		0.74		ps
tjit(Ø)	RMS Phase Jitter (Random); NOTE 1	187.5MHz @ Integration Range: 637kHz - 10MHz		0.48		ps
		212.5MHz @ Integration Range: 637kHz - 10MHz		0.70		ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	175		500	ps
odc	Output Duty Cycle	FREQ_SEL = 1	48		52	%
louc	Output Duty Cycle	FREQ_SEL = 0	45		55	%

NOTE 1: Please refer to the Phase Noise Plots following this section.

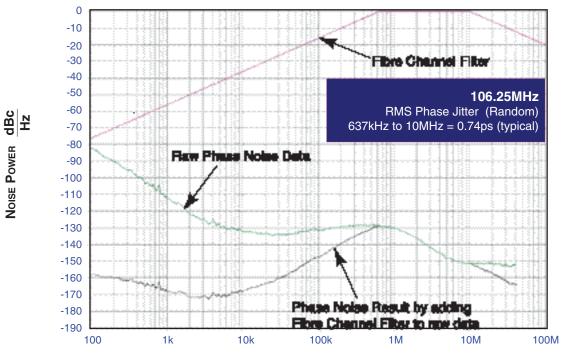
Table 5B. AC Characteristics, $V_{_{DD}} = V_{_{DDA}} = 2.5V \pm 5\%, Ta = 0^{\circ}C$ to $70^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{out}	Output Frequency		81.66		226.66	MHz
		106.25MHz @ Integration Range: 637kHz - 10MHz		0.97		ps
tjit(Ø)	RMS Phase Jitter (Random); NOTE 1	187.5MHz @ Integration Range: 637kHz - 10MHz		0.58		ps
		212.5MHz @ Integration Range: 637kHz - 10MHz		0.95		ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	175		500	ps
odc	Output Duty Cycle	FREQ_SEL = 1	48		52	%
Jouc	Output Duty Cycle	FREQ_SEL = 0	45		55	%

NOTE 1: Please refer to the Phase Noise Plots following this section.

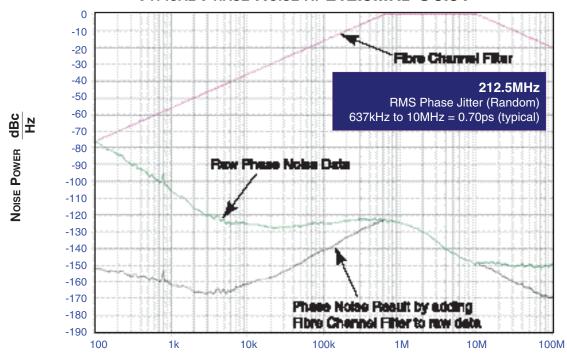






OFFSET FREQUENCY (Hz)

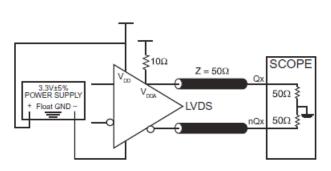
Typical Phase Noise at 212.5MHz @3.3V



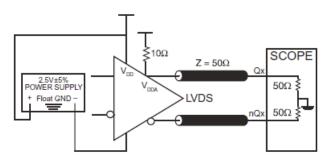
OFFSET FREQUENCY (Hz)



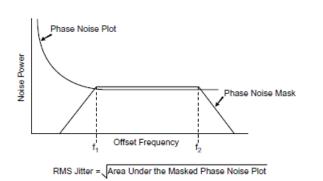
PARAMETER MEASUREMENT INFORMATION



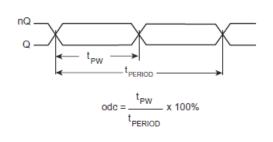
LVDS 3.3V OUTPUT LOAD ACTEST CIRCUIT



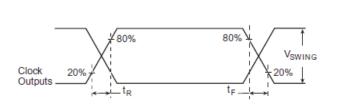
LVDS 2.5V OUTPUT LOAD ACTEST CIRCUIT



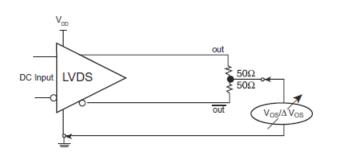
RMS PHASE JITTER



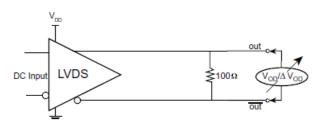
OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD



OUTPUT RISE/FALL TIME



OFFSET VOLTAGE SETUP





APPLICATION INFORMATION

Power Supply Filtering Techniques

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. The 844001 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL. $V_{\scriptscriptstyle DD}$ and $V_{\scriptscriptstyle DDA}$ should be individually connected to the power supply plane through vias, and bypass capacitors should be used for each pin. To achieve optimum jitter performance, power supply isolation is required. Figure 1 illustrates how a 10Ω resistor along with a $10\mu F$ and a $.01\mu F$ bypass capacitor should be connected to each $V_{\scriptscriptstyle DDA}$ pin.

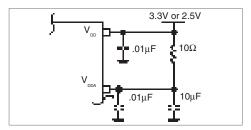


FIGURE 1. POWER SUPPLY FILTERING

CRYSTAL INPUT INTERFACE

The 844001 has been characterized with 18pF parallel resonant crystals. The capacitor values, C1 and C2, shown in *Figure 2* below were determined using a 26.5625MHz, 18pF

parallel resonant crystal and were chosen to minimize the ppm error. The optimum C1 and C2 values can be slightly adjusted for different board layouts.

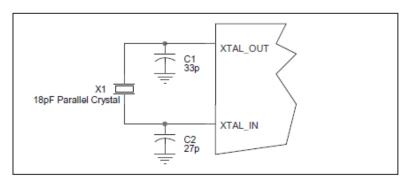


Figure 2. CRYSTAL INPUT INTERFACE



3.3V, 2.5V LVDS DRIVER TERMINATION

A general LVDS interface is shown in Figure 4. In a 100Ω differential transmission line environment, LVDS drivers require a matched load termination of 100Ω across near

the receiver input. For a multiple LVDS outputs buffer, if only partial outputs are used, it is recommended to terminate the unused outputs.

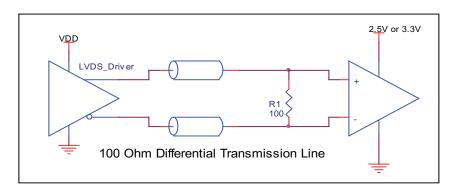


FIGURE 4. TYPICAL LVDS DRIVER TERMINATION



POWER CONSIDERATIONS

This section provides information on power dissipation and junction temperature for the 844001. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 844001 is the sum of the core power plus the power dissipated in the load(s).

The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C.

The equation for Tj is as follows: Tj = θ_{JA} * Pd_total + T_A

Tj = Junction Temperature

 θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming a moderate air flow of 1 meter per second and a multi-layer board, the appropriate value is 90.5° C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 70° C with all outputs switching is: 70° C + 0.440W *90.5°C/W = 109.8°C. This is well below the limit of 125°C.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow, and the type of board (single layer or multi-layer).

Table 6. Thermal Resistance θ_{JA} for 8-Pin TSSOP, Forced Convection

θ_{JA} by Velocity (Meters per Second)

 0
 1
 2.5

 Multi-Layer PCB, JEDEC Standard Test Boards
 101.7°C/W
 90.5°C/W
 89.8°C/W



RELIABILITY INFORMATION

Table 7. $\theta_{_{JA}} \text{vs. Air Flow Table for 8 Lead TSSOP}$

 $\theta_{\mbox{\tiny JA}}$ by Velocity (Meters per Second)

10

 0
 1
 2.5

 Multi-Layer PCB, JEDEC Standard Test Boards
 101.7°C/W
 90.5°C/W
 89.8°C/W

NOTE: An airflow of 1 meter per second is strongly recommended.

TRANSISTOR COUNT

The transistor count for 844001 is: 2533



PACKAGE OUTLINE - G SUFFIX FOR 8 LEAD TSSOP

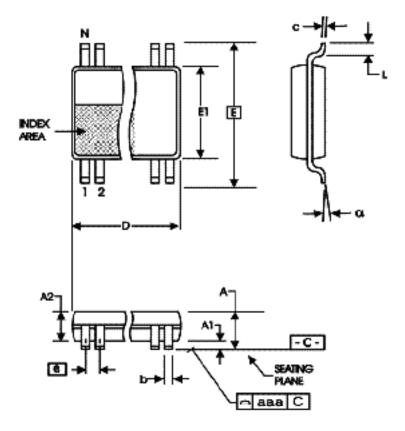


TABLE 8. PACKAGE DIMENSIONS

CVMPOL	Millin	neters
SYMBOL	Minimum	Maximum
N	1	3
А		1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
С	0.09	0.20
D	2.90	3.10
E	6.40 E	BASIC
E1	4.30	4.50
е	0.65 E	BASIC
L	0.45	0.75
α	0°	8°
aaa		0.10

Reference Document: JEDEC Publication 95, MO-153



Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
844001AGLF	001AL	8 lead "Lead-Free" TSSOP	tube	0°C to 70°C
844001AGLFT	001AL	8 lead "Lead-Free" TSSOP	tape & reel	0°C to 70°C



REVISION HISTORY SHEET						
Rev	Table	Page	Description of Change	Date		
А	T4 T9	1 4 8 12	Deleted HiPerClockS references. Crystal Characteristics Table - added note. Deleted application note, LVCMOS to XTAL Interface. Deleted quantity from tape and reel.	9/23/12		
Α	Т9	12	Ordering Information - Removed leaded devices. Updated datasheet header and footer.			
А			Product Discontinuation Notice - Last time buy expires May 6, 2017. PDN CQ-16-01	6/2/16		



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